

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-12 (Canceled)

Claim 13 (Original): A semiconductor device comprising:

a plurality of first semiconductor layers formed in a first region of a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said plurality of first semiconductor layers; and

a second semiconductor layer formed in a second region of said semiconductor substrate.

Claim 14 (Original): A semiconductor device according to claim 13, wherein at least a portion of said second semiconductor layer is formed within the range of a radius of 5 mm from a certain point on said plurality of first semiconductor layers.

Claim 15 (Original): A semiconductor device according to claim 13, wherein each of said plurality of first semiconductor layers is surrounded by said second semiconductor layer.

Claim 16 (Original): A semiconductor device according to claim 13, wherein logic circuits are formed in said plurality of first semiconductor layers, and at least one of a storage element, analog element, and signal input/output circuit is formed in said second semiconductor layer.

Claim 17 (Original): A semiconductor device according to claim 13, wherein said plurality of first semiconductor layers are arranged to be symmetrical with respect to a certain point on said semiconductor substrate.

Claim 18 (Original): A semiconductor device according to claim 13, wherein said plurality of first semiconductor layers are arranged to be symmetrical with respect to a certain straight line on said semiconductor substrate.

Claim 19 (Original): A semiconductor device according to claim 13, wherein the area of said second semiconductor layer is larger than the sum of the areas of said plurality of first semiconductor layers.

Claim 20 (Original): A semiconductor device according to claim 13, wherein said second semiconductor layer is deposited by epitaxial growth.

Claim 21 (Original): A semiconductor device comprising:
a first semiconductor layer formed on a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said first semiconductor layer, said first semiconductor layer being a rectangle; and
a second semiconductor layer formed on an outerperipheral of said semiconductor substrate, said second semiconductor layer surrounding said first semiconductor layer, said second semiconductor layer extending to a corner of said first semiconductor layer.

Claim 22 (Original): A semiconductor device according to claim 21, wherein the area of said second semiconductor layer is larger than the area of said first semiconductor layer.

Claim 23 (Original): A semiconductor device according to claim 21, wherein said second semiconductor layer is deposited by epitaxial growth.

Claim 24 (Original): A semiconductor device comprising:

a first semiconductor layer formed in a first region of a semiconductor substrate with an insulating film interposed between said semiconductor substrate and said first semiconductor layer; and

a second semiconductor layer formed in a second region of said semiconductor substrate, at least a portion of said second semiconductor layer being formed within the range of a radius of 5 mm from any point on said first semiconductor layer.